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from about 2.0 to 2.5% by weight, and a balance of selenium.

5. A semiconductive composition as defined in claim 4 comprising about 5% by weight of tellurium, about 4% by weight of germanium, about 3% by weight of neodymium, about 2.24% by weight of gallium and a balance of selenium. 5

6. A semiconductive composition as set forth in claim 1 comprising tellurium in the range of from about 4.75 to 5.5% by weight, neodymium in the range of from about 4.0 to 4.5% by weight, rubidium in the range of from about 5.5 to 7.0% by weight, and a balance of germanium. 10

7. A semiconductive composition as defined in claim 6 comprising about 5% by weight of tellurium, about 4% by weight of neodymium, about 6% by weight of rubidium, and a balance of germanium. 15

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